

Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 9.6~10.6GHz
- Typical Pout : 54dBm
- Typical Gain: 8dB
- Typical PAE: 40%
- Bias: 40V/-2.4V
- Package: Metal Ceramic

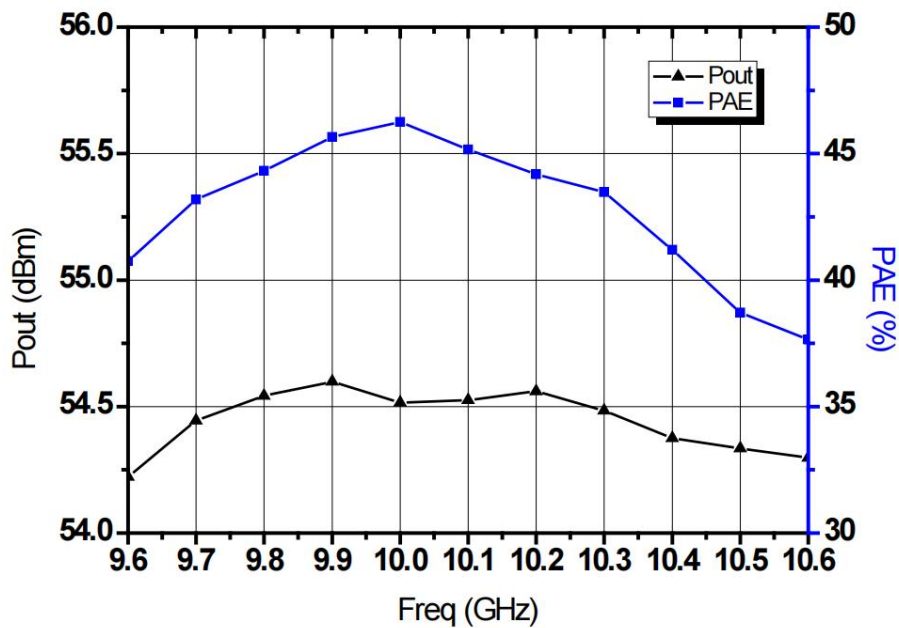


Electrical Specifications (TA=25°C,Vd=40V,Vg= -2.4V,PL=300us,D.C=20%)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	54	-	dBm
Gp	Power Gain	-	8	-	dB
η_{add}	Power Added Efficiency	-	40	-	%

Test Curves

Pout&PAE&Freq.

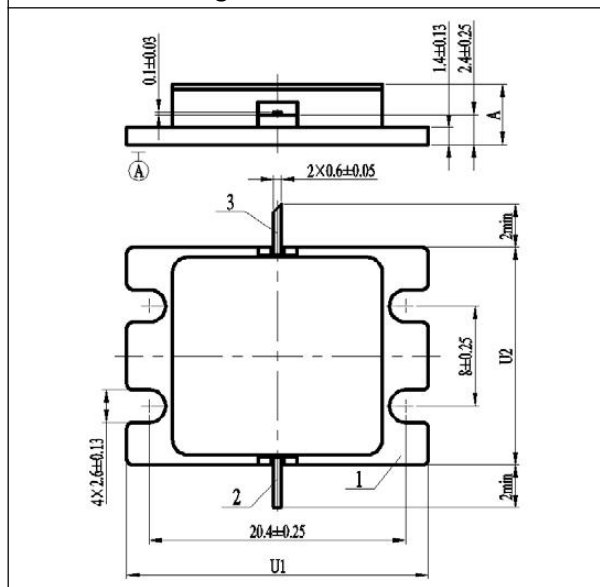


Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Voltage	60V	
V _g	Grid Voltage	-5V	
P _d	DC Dissipation	80W	25°C
T _{ch}	Channel Temperature	225°C	【1】
T _m	Mounting Temperature	280°C	1 min, N ₂ Protection
T _{stg}	Storage Temperature	-55~175°C	
T _c	Operating Temperature	-50~85°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

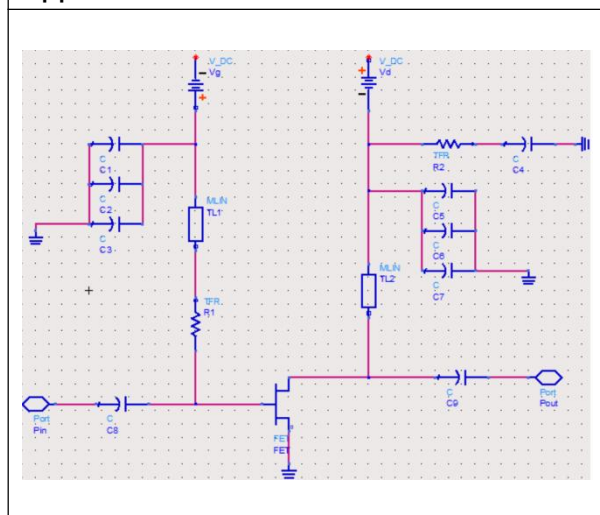
Outline Drawing



Dimension Symbol

Symbol	Value (unit: mm)	
	Min.	Max.
U1	23.80	24.20
U2	17.20	17.60
A	-	5.2

Application Circuit



Pad Definition

Parameter	Symbol	Value	Unit
Filter capacitor	C1,C2,C4,C5,C6	1000	pF
Filter capacitor	C3,C7	100	pF
DC isolation capacitance	C8,C9	1	pF
Stabilizing resistance	R1	15	Ω
Resistance	R2	50	Ω
Microstrip line	TL1,TL2	λ/4	-

Note:

- (1) This product is an internal matching tube, and the input and output impedance values are both 50 ohms;
- (2) Please strictly follow the order of adding negative electricity first and then positive electricity in the power-on sequence. When de-energizing, first reduce the drain voltage and then reduce the gate voltage;
- (3) This product is a high-power device. It is necessary to pay attention to heat dissipation during use. The higher the case temperature, the shorter the service life. It is advisable to use the temperature not higher than 80 degrees;
- (4) This product is an electrostatic sensitive device. It is necessary to pay attention to electrostatic protection during storage and use, and it needs to be well grounded when using it.